EAST Search History

S9	6113	(("a silicon") or ("a Si") or ("aSi") or ("a-Si") or ("a-silicon") or ("amorphous silicon") or ("amorphous Si") or ("amorphous-silicon") or ("amorphous-Si")) NEAR (("poly-silicon") or ("poly-Si") or ("poly silicon") or ("poly Si") or ("polysilicon"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:01
S10	5174	S9 AND ((metal induc$3 (crystallization or recrystallization)) OR (metal induc$3 lateral (crystallization or recrystallization)) or "MIC" or "MILC")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:02
S11	2103	S10 AND ("thin film transistor" or "TFT" or "thin-film-transistor" or "TFTs" or "thin film transistors" or "thin-film-transistors")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:04
S12	716	S11 AND (PR or photoresist or photoresists or "photo-resist" or "photo resist" or "photo-resists" or "photo resists")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:04
S13	485	S12 AND ((source or drain) near electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:05
S14	296	S13 AND ("438".clas. or "257".clas.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/23 12:06
S15	15991	(438/149,151,166,150,300,308,482, 486,487,479,585,586,658,660,662, 663,669,671,684,686,795,798,948, 945,950).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/25 08:18

EAST Search History

S16	82380	(amorphous near3 (silicon or Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 08:18
S17	5132	S16 AND S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 08:18
S18	2554	((oxide or blocking) near3 layer) AND S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 08:19
S19	524	S18 AND ((photoresist or PR or photo-resist or (photo adj resist)) near3 (layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 08:20
S20	35	S19 AND (metal near induced near crystalliz$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 10:50
S21	19	("20020058365"|"20020068390"|"20030032210"|"4997780"|"5904509"|"6218220"|"6396147"|"6514803"|"6521491").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/25 11:05
S22	152	((thin near film near transistor) OR TFT OR thin-film-transistor OR "thin film transistor") with (a-Si or "a Si" or "a silicon" or a-Silicon or amorphous-Si or amorphous-silicon or "amorphous silicon") with (photoresist or photo-resist or PR or (photo adj resist) or photo-resist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 08:55

S23	52	S22 and (crystall$7 or recrystall$7)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 07:38
S24	19	(crystall$8 or recrystall$8) with ((thin near film near transistor) OR TFT OR thin-film-transistor OR "thin film transistor") with (a-Si or "a Si" or "a silicon" or a-Silicon or amorphous-Si or amorphous-silicon or "amorphous silicon") with (photoresist or photo-resist or PR or (photo adj resist) or photo-resist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 11:04
S25	16007	(438/149,151,166,150,300,308,482, 486,487,479,585,586,658,660,662, 663,669,671,684,686,795,798,948, 945,950).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/30 08:55
S26	30	S22 AND S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 08:55
S27	9	("20040026738" | "4330363" | "4592799" | "5021119" | "5395481" | "5589406" | "6100119" | "6495405" | "6689647").PN. OR ("7109075").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/01/30 09:14
S28	4	("20020153527" | "20020192884" | "6194255").PN. OR ("6586287"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/01/30 10:31
S29	2	("20020030188").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/30 11:03

S30	131	(crystall$8 or recrystall$8) same ((thin near film near transistor) OR TFT OR thin-film-transistor OR "thin film transistor") same (a-Si or "a Si" or "a silicon" or a-Silicon or amorphous-Si or amorphous-silicon or "amorphous silicon") same (photoresist or photo-resist or PR or (photo adj resist) or photo-resist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 11:18
S31	8	(crystall$8 or recrystall$8) same ((thin near film near transistor) OR TFT OR thin-film-transistor OR "thin film transistor") same (a-Si or "a Si" or "a silicon" or a-Silicon or amorphous-Si or amorphous-silicon or "amorphous silicon") same (photoresist or photo-resist or PR or (photo adj resist) or photo-resist) same (oxide near3 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 11:12
S32	5	S30 AND (reflow or re-flow or "re flow")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/30 11:19